

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	702/57.ccls. and (insulating\$4 near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 11:53
L2	8	324/671.ccls. and (insulating\$4 near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 11:53
L3	0	324/455.ccls. and (insulating\$4 near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 11:54
L4	68	324/765.ccls. and (insulating\$4 near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 11:54
L5	68	438/16.ccls. and (insulating\$4 near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 11:54
L6	99	438/17.ccls. and (insulating\$4 near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 11:54
L7	0	((insulating\$4 near film) and (surface near voltage\$3) and charge and deposition and average\$4).CLM.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 11:56
L8	0	((insulating\$4 near film) and (surface near voltage\$3) and charge and deposition).CLM.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 11:56

S1	0	702/57.ccls. and (insulating near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:45
S2	2	702/57.ccls. and (insulating near film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 16:05
S3	46609	(insulating near film) and thickness and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 16:06
S4	7967	S3 and voltage and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 16:07
S5	2733	S4 and charge and deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 16:07
S6	2620	S5 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 16:08
S7	687	S6 and leak	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 16:08
S8	367	S7 and uniform	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 16:11

S9	309	substrate and film and thickness and nitrogen and charge and deposition and (surface near voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 16:27
S10	46	substrate and film and thickness and nitrogen and charge and deposition and (surface near voltage)and (non near contact)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 17:13
S17	3731	(measure or test) and (contactless or (non adj contact)) and oxide and film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 17:15
S18	80	S17 and insulate and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 17:17
S19	24422	((dielectric or insulating) with film) and substrate and thickness and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:11
S20	5571	((dielectric and insulating) with film) and substrate and thickness and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:30
S21	1195	S20 and (surface with voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:11
S22	614	S21 and charge and deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:12

S23	7	S22 and leaky	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:13
S24	577	S22 and current	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:13
S25	560	S24 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:15
S26	62	S20 and S21 and S22 and S24 and S25 and (contactless or non-contact)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:16
S27	0	((dielectric and insulating) with film with measuring with thickness) and substrate and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:30
S28	90	((dielectric or insulating) with film with measuring with thickness) and substrate and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/22 14:31
S30	176	substrate and (dielectric near film) and (electrical near measurement)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 11:22
S31	116	substrate and (dielectric near film) and (electrical near measurement) and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 11:58

S32	9	substrate and (dielectric near film) and (electrical near measurement) and voltage and (kelvin or monroe with probe)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:11
S33	0	"6680621".uref.	USPAT; USOCR	OR	OFF	2005/03/23 14:56
S34	0	"6597193".uref.	USPAT; USOCR	OR	OFF	2005/03/23 14:33
S35	93	substrate and (dielectric near film) and voltage and (kelvin or monroe with probe)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:11
S39	29	contactless and characterization and (dielectric with film) and voltage and thickness	USPAT; USOCR	OR	ON	2005/03/23 17:51
S77	61	324/765.ccls. and (insulating near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:22
S78	8	324/671.ccls. and (insulating near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:22
S79	0	324/455.ccls. and (insulating near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:26
S80	65	438/16.ccls. and (insulating near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:23
S81	90	438/17.ccls. and (insulating near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:25

S83	24	324/455.ccls. and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:26
S84	0	non-contact and substrate and nitrogen\$3 and voltage\$3 and (charge near deposition\$4) and (insulating\$4 near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:47
S85	6	substrate and nitrogen\$3 and voltage\$3 and (charge near deposition\$4) and (insulating\$4 near film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:48
S86	7851	substrate and nitrogen\$3 and voltage\$3 and (charge and deposition\$4) and (insulating\$4 and film) and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:49
S87	321	S86 and non-contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:49
S88	909	S86 and corona	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:49
S89	135	S87 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:52
S90	116	"702"/\$.ccls. and corona	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:06

S91	0	(nitrogen near characteristics) and (insulating\$4 near film) and (oxide near thickness) and (optical near thickness) and leakage\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:07
S92	3	nitrogen and (insulating\$4 near film) and (oxide near thickness) and (optical near thickness) and leakage\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 16:41
S93	149415	nitrogen\$4 and oxide and film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 16:41
S94	33244	S93 and (nitride and thickness)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 16:42
S95	2126	S94 and optical and leakage\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 16:42
S96	1621	S95 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 16:43
S97	90	S96 and dose and percentage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:32